Non-Inverting Level Translator, Dual-Supply, 4-Bit

The NLSV4T244 is a 4-bit configurable dual-supply voltage level translator. The input A_n and output B_n ports are designed to track two different power supply rails, V_{CCA} and V_{CCB} respectively. Both supply rails are configurable from 0.9 V to 4.5 V allowing universal low-voltage translation from the input A_n to the output B_n port.

Features

- Wide V_{CCA} and V_{CCB} Operating Range: 0.9 V to 4.5 V
- High-Speed w/ Balanced Propagation Delay
- Inputs and Outputs have OVT Protection to 4.5 V
- Non-preferential V_{CCA} and V_{CCB} Sequencing
- Outputs at 3-State until Active V_{CC} is Reached
- Power-Off Protection
- Outputs Switch to 3-State with V_{CCB} at GND
- Ultra-Small Packaging: 1.7 mm x 2.0 mm UQFN12
- NLVSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These are Pb–Free Devices

Typical Applications

• Mobile Phones, PDAs, Other Portable Devices

Important Information

• ESD Protection for All Pins: HBM (Human Body Model) > 1500 V



ON Semiconductor®

www.onsemi.com

MARKING DIAGRAMS



UQFN12 MU SUFFIX CASE 523AE



UR = Specific Device Code

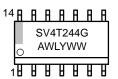
M = Date Code

= Pb–Free Package

(Note: Microdot may be in either location)



SOIC-14 D SUFFIX CASE 751A





TSSOP-14 DT SUFFIX CASE 948G



A = Assembly Location

L, WL = Wafer Lot Y, YY = Year W, WW = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

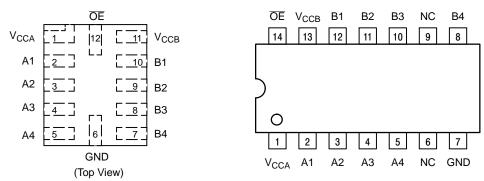


Figure 1. Pin Assignments

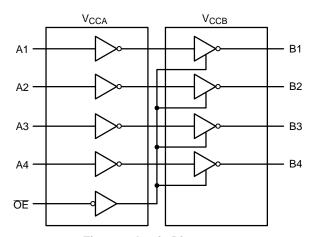


Figure 2. Logic Diagram

PIN ASSIGNMENT

PIN	FUNCTION
V _{CCA}	Input Port DC Power Supply
V _{CCB}	Output Port DC Power Supply
GND	Ground
A _n	Input Port
B _n	Output Port
ŌĒ	Output Enable

TRUTH TABLE

In	Outputs	
ŌĒ	A _n	B _n
L	L	L
L	Н	Н
Н	Х	3-State

ORDERING INFORMATION

Device	Package	Shipping [†]		
NLSV4T244MUTAG	UQFN12	2000 / Tapa and Book		
NLVSV4T244MUTAG*	(Pb-Free)	3000 / Tape and Reel		
NLSV4T244DR2G	SOIC-14 (Pb-Free)	2500 / Tape and Reel		
NLSV4T244DTR2G	TSSOP-14 (Pb-Free)	2500 / Tape and Reel		

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

^{*}NLVSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

MAXIMUM RATINGS

Symbol	Rating		Value	Condition	Unit
V _{CCA} , V _{CCB}	DC Supply Voltage		-0.5 to +5.5		V
VI	DC Input Voltage	A _n	-0.5 to +5.5		V
V _C	Control Input	OE	-0.5 to +5.5		V
Vo	DC Output Voltage (Power Down)	B _n	-0.5 to +5.5	$V_{CCA} = V_{CCB} = 0$	V
	(Active Mode)	B _n	-0.5 to +5.5		V
	(Tri-State Mode)	B _n	-0.5 to +5.5		V
I _{IK}	DC Input Diode Current		-20	V _I < GND	mA
lok	DC Output Diode Current		-50	V _O < GND	mA
Io	DC Output Source/Sink Current		±50		mA
I _{CCA} , I _{CCB}	DC Supply Current Per Supply Pin		±100		mA
I _{GND}	DC Ground Current per Ground Pin		±100		mA
T _{STG}	Storage Temperature		-65 to +150		°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CCA} , V _{CCB}	Positive DC Supply Voltage		0.9	4.5	V
VI	Bus Input Voltage		GND	4.5	V
V_{C}	Control Input	ŌĒ	GND	4.5	V
V_{IO}	Bus Output Voltage (Power Down Mode)	B _n	GND	4.5	V
	(Active Mode)	B _n	GND	V _{CCB}	V
	(Tri-State Mode)	B _n	GND	4.5	V
T_A	Operating Temperature Range	-40	+105	°C	
Δt / ΔV	Input Transition Rise or Rate V _I , from 30% to 70% of V _{CC} ; V _{CC} = 3.3 V ± 0.3 V		0	10	nS

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

					-40°C to	o +85°C	
Symbol	Parameter	Test Conditions	V _{CCA} (V)	V _{CCB} (V)	Min	Max	Unit
V _{IH}	Input HIGH Voltage		3.6 – 4.5	0.9 – 4.5	2.2	_	V
	(An, \overline{OE})		2.7 – 3.6		2.0	_	
			2.3 – 2.7		1.6	_	
			1.4 – 2.3		0.65 * V _{CCA}	_	
			0.9 – 1.4		0.9 * V _{CCA}	_	
V_{IL}	Input LOW Voltage		3.6 – 4.5	0.9 – 4.5	-	0.8	V
	(An, \overline{OE})		2.7 – 3.6		-	0.8	
			2.3 – 2.7		-	0.7	
			1.4 – 2.3		-	0.35 * V _{CCA}	
			0.9 – 1.4		-	0.1 * V _{CCA}	
V _{OH}	Output HIGH Voltage	$I_{OH} = -100 \mu A; V_I = V_{IH}$	0.9 - 4.5	0.9 – 4.5	V _{CCB} – 0.2	_	V
		$I_{OH} = -0.5 \text{ mA}; V_I = V_{IH}$	0.9	0.9	0.75 * V _{CCB}	_	
		$I_{OH} = -2 \text{ mA}; V_I = V_{IH}$	1.4	1.4	1.05	_	
		$I_{OH} = -6 \text{ mA}; V_I = V_{IH}$	1.65	1.65	1.25	_	
			2.3	2.3	2.0	_	
		$I_{OH} = -12 \text{ mA}; V_I = V_{IH}$	2.3	2.3	1.8	_	
			2.7	2.7	2.2	_	
		$I_{OH} = -18 \text{ mA}; V_I = V_{IH}$	2.3	2.3	1.7	_	
			3.0	3.0	2.4	_	
		$I_{OH} = -24 \text{ mA}; V_I = V_{IH}$	3.0	3.0	2.2	_	
V _{OL}	Output LOW Voltage	$I_{OL} = 100 \mu A; V_I = V_{IL}$	0.9 – 4.5	0.9 – 4.5	-	0.2	V
		$I_{OL} = 0.5 \text{ mA}; V_I = V_{IL}$	1.1	1.1	-	0.3	
		$I_{OL} = 2 \text{ mA}; V_I = V_{IL}$	1.4	1.4	-	0.35	
		$I_{OL} = 6 \text{ mA}; V_I = V_{IL}$	1.65	1.65	-	0.3	
		I_{OL} = 12 mA; V_I = V_{IL}	2.3	2.3	-	0.4	
			2.7	2.7	-	0.4	
		I_{OL} = 18 mA; V_I = V_{IL}	2.3	2.3	-	0.6	
			3.0	3.0	-	0.45	
		I_{OL} = 24 mA; V_I = V_{IL}	3.0	3.0	-	0.6	
l _l	Input Leakage Current	$V_I = V_{CCA}$ or GND	0.9 – 4.5	0.9 – 4.5	-1.0	1.0	μΑ
l _{OFF}	Power-Off Leakage Current	OE = 0 V	0 0.9 – 4.5	0.9 – 4.5 0	-1.0 -1.0	1.0 1.0	μΑ
I _{CCA}	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$, $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	2.0	μΑ
I _{CCB}	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$, $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	2.0	μΑ
_{CCA} + I _{CCB}	Quiescent Supply Current	$V_I = V_{CCA}$ or GND; $I_O = 0$, $V_{CCA} = V_{CCB}$	0.9 – 4.5	0.9 – 4.5	-	4.0	μΑ
ΔI_{CCA}	Increase in I _{CC} per Input Voltage, Other Inputs at V _{CCA} or GND	$V_I = V_{CCA} - 0.6 \text{ V};$ $V_I = V_{CCA} \text{ or GND}$	4.5 3.6	4.5 3.6	_	10 5.0	μΑ
ΔI_{CCB}	Increase in I _{CC} per Input Voltage, Other Inputs at V _{CCA} or GND	$V_I = V_{CCA} - 0.6 \text{ V};$ $V_I = V_{CCA} \text{ or GND}$	4.5 3.6	4.5 3.6	-	10 5.0	μΑ
l _{OZ}	I/O Tri–State Output Leakage Current	$T_A = 25^{\circ}C, \overline{OE} = V_{CCA}$	0.9 – 4.5	0.9 – 4.5	-1.0	1.0	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TOTAL STATIC POWER CONSUMPTION ($I_{CCA} + I_{CCB}$)

					-40°C to	o +85°C					
					V _{CCI}	_B (V)					
	4.	.5	3	.3	2.	.8	1.	.8	0.	.9	
V _{CCA} (V)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
4.5		2		2		2		2		< 1.5	μΑ
3.3		2		2		2		2		< 1.5	μΑ
2.8		< 2		< 1		< 1		< 0.5		< 0.5	μΑ
1.8		< 1		< 1		< 0.5		< 0.5		< 0.5	μΑ
0.9		< 0.5		< 0.5		< 0.5		< 0.5		< 0.5	μΑ

NOTE: Connect ground before applying supply voltage V_{CCA} or V_{CCB}. This device is designed with the feature that the power–up sequence of V_{CCA} and V_{CCB} will not damage the IC.

AC ELECTRICAL CHARACTERISTICS

							-40°C t	o +85°C					
							V _{CC}	_B (V)					
			4.	.5	3	.3	2	.8	1	.8	1.	.2	
Symbol	Parameter	V _{CCA} (V)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
t _{PLH} ,	Propagation	4.5		1.6		1.8		2.0		2.1		2.3	nS
t _{PHL} (Note 1)	Delay,	3.3		1.7		1.9		2.1		2.3		2.6	
(Note 1)	A _n to B _n	2.8		1.9		2.1		2.3		2.5		2.8	
		1.8		2.1		2.4		2.5		2.7		3.0	
		1.2		2.4		2.7		2.8		3.0		3.3	
t _{PZH} ,	Output	4.5		2.6		3.8		4.0		4.1		4.3	nS
t _{PZL} (Note 1)	Enable,	3.3		3.7		3.9		4.1		4.3		4.6	
(Note 1)	OE to B _n	2.5		3.9		4.1		4.3		4.5		4.8	
		1.8		4.1		4.4		4.5		4.7		5.0	
		1.2		4.4		4.7		4.8		5.0		5.3	
t _{PHZ} ,	Output	4.5		2.6		3.8		4.0		4.1		4.3	nS
t _{PLZ}	Disable,	3.3		3.7		3.9		4.1		4.3		4.6	
(Note 1)	OE to B _n	2.5		3.9		4.1		4.3		4.5		4.8	
		1.8		4.1		4.4		4.5		4.7		5.0	
		1.2		4.4		4.7		4.8		5.0		5.3	
t _{OSHL} ,	Output to	4.5		0.15		0.15		0.15		0.15		0.15	nS
toslh	Output Skew,	3.3		0.15		0.15		0.15		0.15		0.15	
(Note 1)	Time	2.5		0.15		0.15		0.15		0.15		0.15	
		1.8		0.15		0.15		0.15		0.15		0.15	
		1.2		0.15		0.15		0.15		0.15		0.15	

^{1.} Propagation delays defined per Figure 3.

CAPACITANCE

Symbol	Parameter	Test Conditions	Typ (Note 2)	Unit
C _{IN}	Control Pin Input Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA/B}$	3.5	pF
C _{I/O}	I/O Pin Input Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA/B}$	5.0	pF
C _{PD}	Power Dissipation Capacitance	$V_{CCA} = V_{CCB} = 3.3 \text{ V}, V_I = 0 \text{ V or } V_{CCA}, f = 10 \text{ MHz}$	20	pF

Typical values are at T_A = +25°C.
 C_{PD} is defined as the value of the IC's equivalent capacitance from which the operating current can be calculated from: I_{CC(operating)} ≅ C_{PD} x V_{CC} x f_{IN} x N_{SW} where I_{CC} = I_{CCA} + I_{CCB} and N_{SW} = total number of outputs switching.

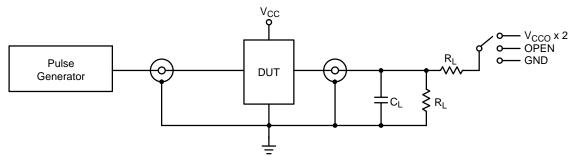


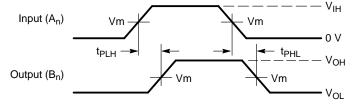
Figure 3. AC (Propagation Delay) Test Circuit

Test	Switch
t _{PLH} , t _{PHL}	OPEN
t _{PLZ} , t _{PZL}	V _{CCO} x 2
t _{PHZ} , t _{PZH}	GND

C_L = 15 pF or equivalent (includes probe and jig capacitance)

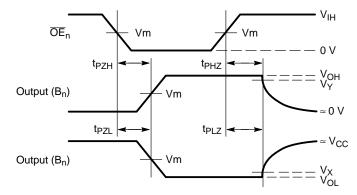
 $R_L = 2 k\Omega$ or equivalent

 Z_{OUT} of pulse generator = 50 Ω



Waveform 1 – Propagation Delays

 $t_R = t_F = 2.0 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$



Waveform 2 - Output Enable and Disable Times

 $t_R = t_F = 2.0 \text{ ns}, 10\% \text{ to } 90\%; f = 1 \text{ MHz}; t_W = 500 \text{ ns}$

Figure 4. AC (Propagation Delay) Test Circuit Waveforms

	V _{CC}						
Symbol	3.0 V – 4.5 V	2.3 V – 2.7 V	1.65 V – 1.95 V	1.4 V – 1.6 V	0.9 V – 1.3 V		
V_{mA}	V _{CCA} /2						
V _{mB}	V _{CCB} /2						
V _X	V _{OL} + 10% V _{OH}						
V_{Y}	V _{OH} x 0.9						

UQFN12 1.7x2.0, 0.4P CASE 523AE-01 **ISSUE A**



DATE 11 JUN 2007



PIN 1 REFERENCE

0.10 C

0.10 C

0.05 С

0.05 C **TOP VIEW**

A1

SIDE VIEW

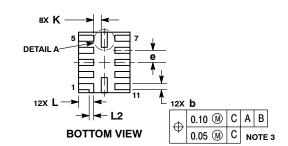
2X |

12X 🗀





DETAIL B OPTIONAL CONSTRUCTION

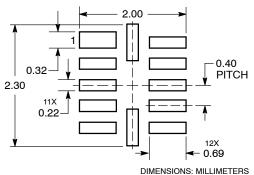


DETAIL B

SEATING PLANE

-A B

MOUNTING FOOTPRINT SOLDERMASK DEFINED



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME
- Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM
- FROM TERMINAL TIP.

 MOLD FLASH ALLOWED ON TERMINALS

 ALONG EDGE OF PACKAGE. FLASH 0.03

 MAX ON BOTTOM SURFACE OF
- TERMINALS.
 DETAIL A SHOWS OPTIONAL
 CONSTRUCTION FOR TERMINALS.

	MILLIMETERS						
DIM	MIN	MAX					
Α	0.45	0.55					
A1	0.00	0.05					
A3	0.127	REF					
b	0.15	0.25					
D	1.70	BSC					
Е	2.00	BSC					
е	0.40	BSC					
K	0.20						
L	0.45	0.55					
L1	0.00	0.03					
L2	0.15	REF					

GENERIC MARKING DIAGRAM*



XX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98AON23418D	Electronic versions are uncontrolled except when accessed directly from the Document Reposi Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	UQFN12 1.7 X 2.0, 0.4P		PAGE 1 OF 1

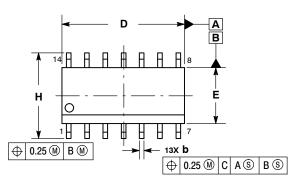
ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

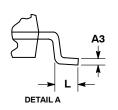


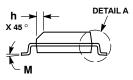
0.10

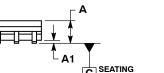
SOIC-14 NB CASE 751A-03 ISSUE L

DATE 03 FEB 2016









- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
 - ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
АЗ	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
е	1.27 BSC		0.050 BSC	
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
Ĺ	0.40	1.25	0.016	0.049
М	0 °	7°	0 °	7°

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator. "G" or microdot " ■". may or may not be present.

-	— 6.50 —		14X
1		←	- 1.18
			_ 1.27
→			v PITCH
14X 0.58			
0.58 -	i		

SOLDERING FOOTPRINT*

DIMENSIONS: MILLIMETERS *For additional information on our Pb-Free strategy and soldering

details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42565B	Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOIC-14 NB		PAGE 1 OF 2

ON Semiconductor and un are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

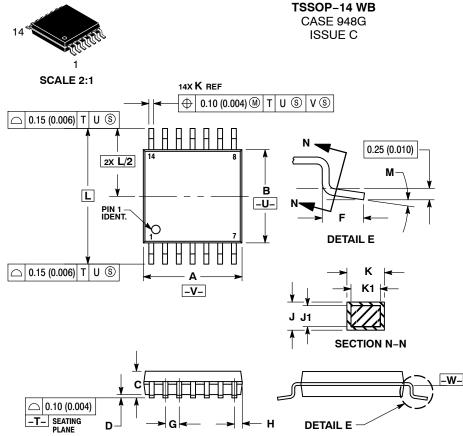
SOIC-14 CASE 751A-03 ISSUE L

DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

DOCUMENT NUMBER:	98ASB42565B	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOIC-14 NB		PAGE 2 OF 2

ON Semiconductor and IN are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.



DATE 17 FEB 2016

- NOTES.

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

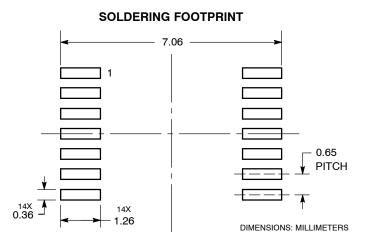
 3. DIMENSION A DOES NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

 6. TERMINAL NUMBERS ARE SHOWN FOR DEFERENCE ONLY
- REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE
 DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INC	INCHES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252	BSC	
M	0 °	8 °	o °	a °	

GENERIC MARKING DIAGRAM*





= Assembly Location

= Wafer Lot

= Year W = Work Week

= Pb-Free Package (Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98ASH70246A	Electronic versions are uncontrolled except when accessed directly from the Document Reposito Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	TSSOP-14 WB		PAGE 1 OF 1

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer pu

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

a Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Translation - Voltage Levels category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below:

NLSX4373DMR2G NLSX5012MUTAG NLSX0102FCT2G NLSX4302EBMUTCG PCA9306FMUTAG MC100EPT622MNG
NLSX5011MUTCG NLV9306USG NLVSX4014MUTAG NLSV4T3144MUTAG NLVSX4373MUTAG NB3U23CMNTAG
MAX3371ELT+T NLSX3013BFCT1G NLV7WBD3125USG NLSX3012DMR2G 74AVCH1T45FZ4-7 NLVSV1T244MUTBG
74AVC1T45GS-Q100H CLVC16T245MDGGREP MC10H124FNG CAVCB164245MDGGREP CD40109BPWR MC10H350FNG
MC10H125FNG MC100EPT21MNR4G MC100EP91DWG NLSX3018MUTAG NLSV2T244MUTAG NLSX3013FCT1G
NLSX5011AMX1TCG PCA9306USG SN74GTL1655DGGR SN74AVCA406LZQSR NLSX4014DTR2G NLSX3018DTR2G
LTC1045CSW#PBF LTC1045CN#PBF SY100EL92ZG 74AXP1T34GMH 74AXP1T34GNH LSF0204DPWR PI4ULS3V204LE
ADG3245BRUZ-REEL7 ADG3123BRUZ ADG3245BRUZ ADG3246BCPZ ADG3308BCPZ-REEL ADG3233BRJZ-REEL7
ADG32233BRMZ